

IN THE CLAIMS:

The status of each claim that has been introduced in the above-referenced application is identified in the ensuing listing of the claims. This listing of the claims replaces all previously submitted claims listings.

1. (Previously Presented) A method for establishing an electrical contact with at least one semiconductor device, comprising:
establishing an electrical contact between a first member of an electrical connector and a contact that is in electrical communication with the at least one semiconductor device; and
drawing the first member toward the contact.
2. (Previously Presented) The method of claim 1, wherein the drawing is effected in a direction substantially normal to a plane of the contact.
3. (Previously Presented) The method of claim 1, wherein the drawing is effected in a direction substantially normal to a plane of a substrate upon which the contact is carried.
4. (Previously Presented) The method of claim 1, wherein the drawing is effected by positioning a second member of the electrical connector opposite the first member.
5. (Previously Presented) The method of claim 4, wherein the drawing is effected by magnetically attracting at least one of the first member and the second member toward at least the other of the first member and the second member.
6. (Previously Presented) The method of claim 4, wherein the drawing comprises securing the first and second members to a substrate upon which the contact is carried.
7. (Previously Presented) The method of claim 1, wherein the drawing comprises magnetically attracting the first member against the contact.

8. (Previously Presented) A method for stress testing a plurality of semiconductor devices carried upon a common substrate and in communication with common ground and power contacts, comprising:

establishing electrical contact between a first member of an electrical connector and at least one contact of the ground contact and the power contact; and
drawing the first member toward the at least one contact.

9. (Previously Presented) The method of claim 8, wherein the drawing is effected in a direction substantially normal to a plane of the substrate.

10. (Withdrawn and currently amended) The method of claim 8, wherein said drawing nonrigidly biases said the first member against said the at least one contact.

11. (Previously Presented) The method of claim 8, wherein the drawing comprises positioning a second member of the electrical connector opposite the substrate from the first member.

12. (Previously Presented) The method of claim 11, wherein at least one of the first member and the second member is drawn toward at least the other of the first member and the second member.

13. (Previously Presented) The method of claim 12, wherein the drawing comprises magnetically attracting at least one of the first member and the second member toward at least the other of the first member and the second member.

14. (Previously Presented) The method of claim 8, wherein the drawing comprises magnetically attracting the first member against the at least one contact.

15. (Previously Presented) The method of claim 8, wherein the drawing comprises securing at least the first member in position relative to the substrate.

16. (Previously Presented) The method of claim 8, further comprising: electrically connecting another first member of another electrical connector to another of the ground contact and the power contact; and drawing the another first member toward the another contact.

17. (Previously Presented) The method of claim 16, further comprising: applying a substantially constant amount of current to each semiconductor device of the plurality of semiconductor devices through the first member and the another first member.

18. (Previously Presented) The method of claim 17, further comprising: heating each of the plurality of semiconductor devices.

19. (Previously Presented) The method of claim 18, wherein the heating comprises cycling a temperature of each of the plurality of semiconductor devices.

20. (Previously Presented) The method of claim 18, wherein the heating comprises varying a temperature of each of the plurality of semiconductor devices.